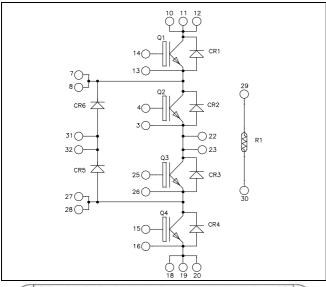
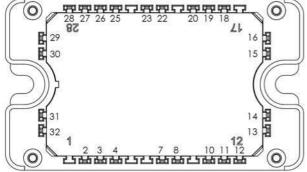


Three level inverter Trench + Field Stop IGBT4







All multiple inputs and outputs must be shorted together Example: 10/11/12; 7/8 ...

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT 4
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Q1 to Q4 Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		1200	V
Τ	Continuous Collector Current	$T_C = 25^{\circ}C$	80	
$I_{\rm C}$		$T_C = 80$ °C	60	A
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Power Dissipation	$T_C = 25^{\circ}C$	280	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Q1 to Q4 Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} =$			1	mA	
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
		$I_C = 50A$	$T_j = 150$ °C		2.2		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.6 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Q1 to Q4 Dynamic Characteristics (per IGBT)

_	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		2770		
Coes	Output Capacitance	$V_{CE} = 25V$		205		pF
Cres	Reverse Transfer Capacitance	f = 1MHz		160		
Q _G	Gate charge	V_{GE} = ±15V; V_{CE} =600V I_{C} =50A		0.38		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		50		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		27		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 50A$		270		ns
T_{f}	Fall Time	$R_G = 8.2\Omega$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)	50		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$		30		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50A$		290		115
T_{f}	Fall Time	$R_G = 8.2\Omega$		80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V \qquad T_{J} = 25^{\circ}C$		3.8		mJ
Lon	Turn-on Switching Energy	$V_{CE} = 600V$ $T_{J} = 150^{\circ}$		5.5		1113
E_{off}	Turn-off Switching Energy	$I_C = 50A$ $T_J = 25^{\circ}C$		2.5		mJ
2011	Time on a mining Energy	$R_G = 8.2\Omega \qquad T_J = 150^{\circ}$	C	4.5		1110
I_{sc}	Short Circuit data	$V_{GE} \le 15V \; ; V_{Bus} = 900V t_p \le 10 \mu s \; ; T_j = 150 ^{\circ} C$		200		A
R_{thJC}	Junction to Case Thermal Resistance				0.53	°C/W



CR1 to CR6 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_{R} = 600V$				100	μA
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		30		A
		$I_F = 30A$			2.6	3.1	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 60A$			3.2		V
		$I_F = 30A$	$T_j = 125$ °C		1.8		V
+	Parama Pasayamy Time	$I_F = 30A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25$ °C		300		***
t _{rr}	Reverse Recovery Time		$T_j = 125$ °C		380		ns
0	Reverse Recovery Charge		$T_j = 25$ °C		360		nC
Q_{rr}			$T_{j} = 125^{\circ}C$		1700		пС
E _{rr}	Reverse Recovery Energy	$\begin{split} I_F = 30A \\ V_R = 800V \\ di/dt = 1000A/\mu s \end{split}$	$T_j = 125$ °C		1.6		mJ
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$			5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$		3952		K
$\Delta B/B$	T _C =100°C		4		%

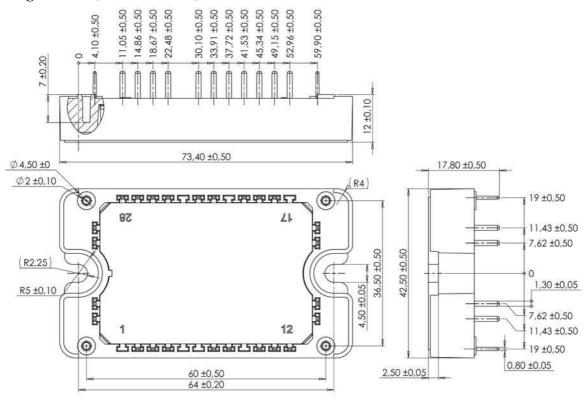
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic	Min	Max	Unit		
V_{ISOL}	RMS Isolation Voltage, any terminal to case	4000		V		
T_{J}	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight	•			110	g

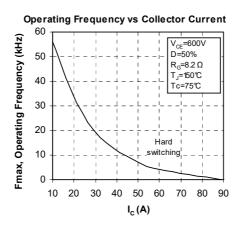


Package outline (dimensions in mm)

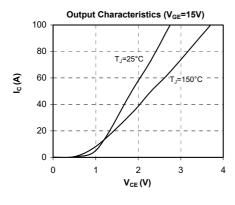


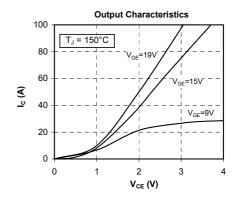
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

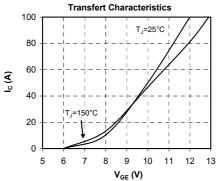
Q1 to Q4 Typical performance curve

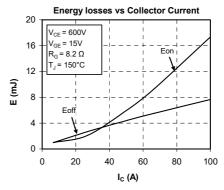


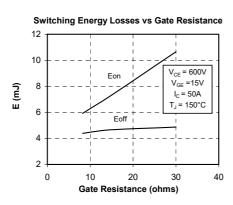


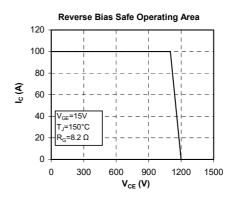


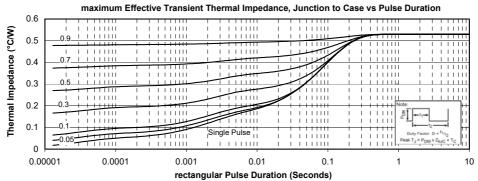






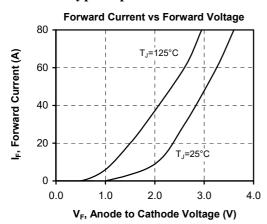




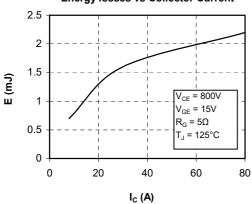




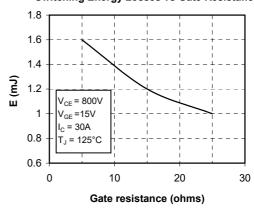
CR1 to CR6 Typical performance curve



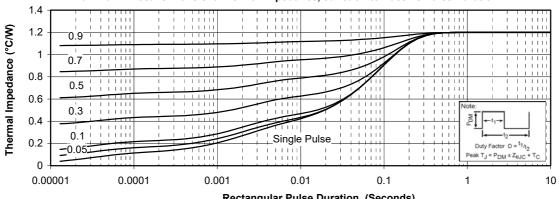
Energy losses vs Collector Current



Switching Energy Losses vs Gate Resistance



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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